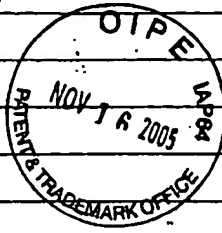


U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.352US0		10/799,060	
				Applicant(s)		Conf. No.	
(Use several sheets if necessary)				Lutze et al.		6740	
(Form PTO-1449)				Filing Date		Art Group	
				March 12, 2004		2818	



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Examiner <i>MA</i>	Date Considered <i>11/28/05</i>
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		Document	Date	Country	Class	Subclass	Yes	No
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<i>YH</i>	069	Takeuchi, Y., et al., "A Self-Aligned STI Process Integration for Low Cost and Highly Reliable 1Gbit Flash Memories," 1998 Symposium on VLSI Technology; Digest of Technical Papers, IEEE, Honolulu, Hawaii, June 9-11, 1998, pp. 102-103.						
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